

# MOSFET – SiC Power, Single N-Channel, D2PAK-7L

1200 V, 160 mΩ, 19.5 A



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## NVBG160N120SC1

### Features

- Typ.  $R_{DS(on)} = 160 \text{ m}\Omega$
- Ultra Low Gate Charge (typ.  $Q_{G(tot)} = 33.8 \text{ nC}$ )
- Low Effective Output Capacitance (typ.  $C_{oss} = 50.7 \text{ pF}$ )
- 100% Avalanche Tested
- Qualified According to AEC-Q101
- This Device is Pb-Free and is RoHS Compliant

### Typical Applications

- Automotive On Board Charger
- Automotive DC/DC converter for EV/HEV

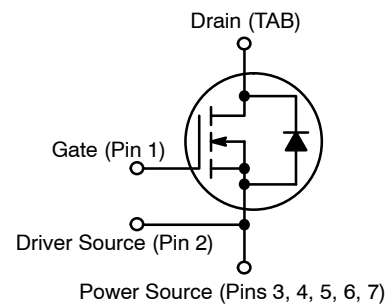
### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	1200	V	
Gate-to-Source Voltage		$V_{GS}$	-15/+25	V	
Recommended Operation Values of Gate – Source Voltage		$T_C < 175^\circ\text{C}$ $V_{GSop}$	-5/+20	V	
Continuous Drain Current (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	$I_D$	19.5	A
			$P_D$	136	W
Continuous Drain Current (Note 1)	Steady State	$T_C = 100^\circ\text{C}$	$I_D$	13.7	A
			$P_D$	68	W
Pulsed Drain Current (Note 2)		$T_A = 25^\circ\text{C}$	$I_{DM}$	78	A
Single Pulse Surge Drain Current Capability	$T_A = 25^\circ\text{C}$ , $t_p = 10 \mu\text{s}$ , $R_G = 4.7 \Omega$		$I_{DSC}$	140	A
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)		$I_S$	13.6	A	
Single Pulse Drain-to-Source Avalanche Energy ( $I_L = 15.5 \text{ A}_{pk}$ , $L = 1 \text{ mH}$ ) (Note 3)		$E_{AS}$	120	mJ	
Maximum Lead Temperature for Soldering, 1/8" from Case for 10 Seconds		$T_L$	300	$^\circ\text{C}$	

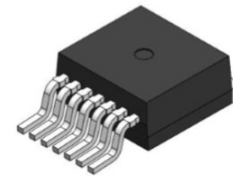
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3.  $E_{AS}$  of 120 mJ is based on starting  $T_J = 25^\circ\text{C}$ ;  $L = 1 \text{ mH}$ ,  $I_{AS} = 15.5 \text{ A}$ ,  $V_{DD} = 120 \text{ V}$ ,  $V_{GS} = 18 \text{ V}$ .

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
1200 V	224 mΩ @ 20 V	19.5 A

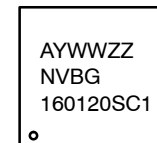


### N-CHANNEL MOSFET



D2PAK-7L  
CASE 418BJ

### MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Lot Traceability
- NVBG160120SC1 = Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

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**Table 1. THERMAL CHARACTERISTICS**

Parameter	Symbol	Max	Units
Thermal Resistance Junction-to-Case (Note 1)	$R_{\theta JC}$	1.1	$^{\circ}C/W$
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	40	$^{\circ}C/W$

**Table 2. ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$  unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 V, I_D = 1 mA$	1200			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 1 mA$ , refer to $25^{\circ}C$		0.7		$V/^{\circ}C$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0 V$ $V_{DS} = 1200 V$	$T_J = 25^{\circ}C$		100	$\mu A$
			$T_J = 175^{\circ}C$		1	mA
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = +25/-15 V, V_{DS} = 0 V$			$\pm 1$	$\mu A$
<b>ON CHARACTERISTICS</b> (Note 2)						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 2.5 mA$	1.8	3	4.3	V
Recommended Gate Voltage	$V_{GOP}$		-5		+20	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 20 V, I_D = 12 A, T_J = 25^{\circ}C$ $V_{GS} = 20 V, I_D = 12 A, T_J = 175^{\circ}C$		160	224	m $\Omega$
				239	365	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 10 V, I_D = 12 A$		5.5		S
<b>CHARGES, CAPACITANCES &amp; GATE RESISTANCE</b>						
Input Capacitance	$C_{ISS}$	$V_{GS} = 0 V, f = 1 MHz,$ $V_{DS} = 800 V$		678		pF
Output Capacitance	$C_{OSS}$			50.7		
Reverse Transfer Capacitance	$C_{RSS}$			5.87		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -5/20 V, V_{DS} = 600 V,$ $I_D = 16 A$		33.8		nC
Threshold Gate Charge	$Q_{G(TH)}$			6.1		
Gate-to-Source Charge	$Q_{GS}$			11.6		
Gate-to-Drain Charge	$Q_{GD}$			9.6		
Gate-Resistance	$R_G$	$f = 1 MHz$		1.39		$\Omega$
<b>SWITCHING CHARACTERISTICS</b> (Note 4)						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -5/20 V, V_{DS} = 800 V,$ $I_D = 16 A, R_G = 6 \Omega,$ Inductive Load		11	20	ns
Rise Time	$t_r$			11	20	
Turn-Off Delay Time	$t_{d(OFF)}$			15	27	
Fall Time	$t_f$			7.4	15	
Turn-On Switching Loss	$E_{ON}$			120		$\mu J$
Turn-Off Switching Loss	$E_{OFF}$			28		
Total Switching Loss	$E_{TOT}$			148		
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Continuous Drain-Source Diode Forward Current	$I_{SD}$	$V_{GS} = -5 V, T_J = 25^{\circ}C$			13.6	A
Pulsed Drain-Source Diode Forward Current (Note 2)	$I_{SDM}$	$V_{GS} = -5 V, T_J = 25^{\circ}C$			78	A
Forward Diode Voltage	$V_{SD}$	$V_{GS} = -5 V, I_{SD} = 6 A, T_J = 25^{\circ}C$		3.9		V

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**Table 2. ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Reverse Recovery Time	$t_{RR}$	$V_{GS} = -5/20\text{ V}$ , $I_{SD} = 16\text{ A}$ , $dI_S/dt = 1000\text{ A}/\mu\text{s}$		15		ns
Reverse Recovery Charge	$Q_{RR}$			47		nC
Reverse Recovery Energy	$E_{REC}$			3.9		$\mu\text{J}$
Peak Reverse Recovery Current	$I_{RRM}$			6.6		A
Charge time	$T_a$			7.0		ns
Discharge time	$T_b$			7.4		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Switching characteristics are independent of operating junction temperature

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## TYPICAL CHARACTERISTICS

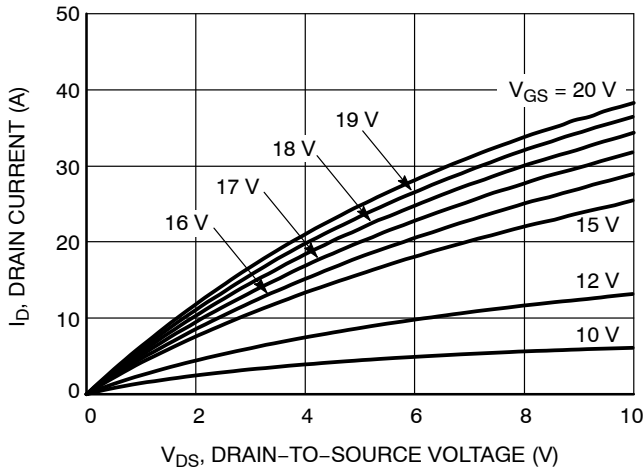


Figure 1. On-Region Characteristics



Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

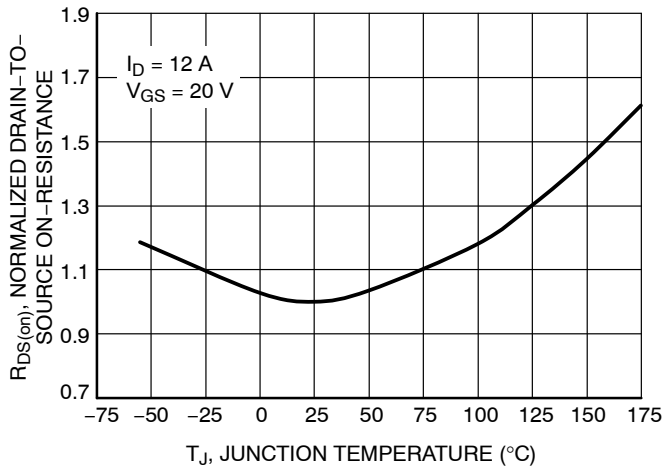


Figure 3. On-Resistance Variation with Temperature

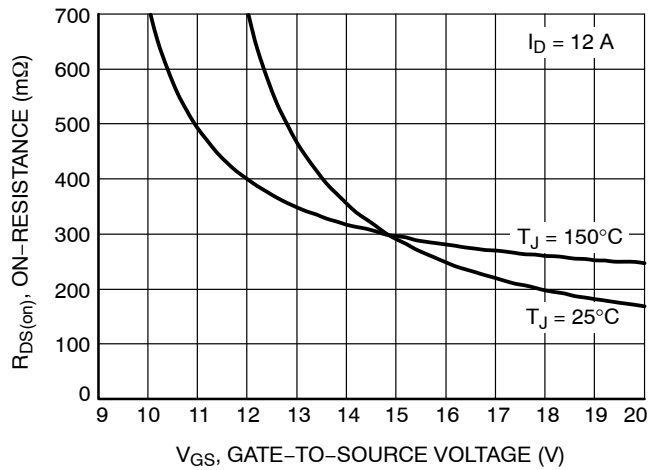


Figure 4. On-Resistance vs. Gate-to-Source Voltage

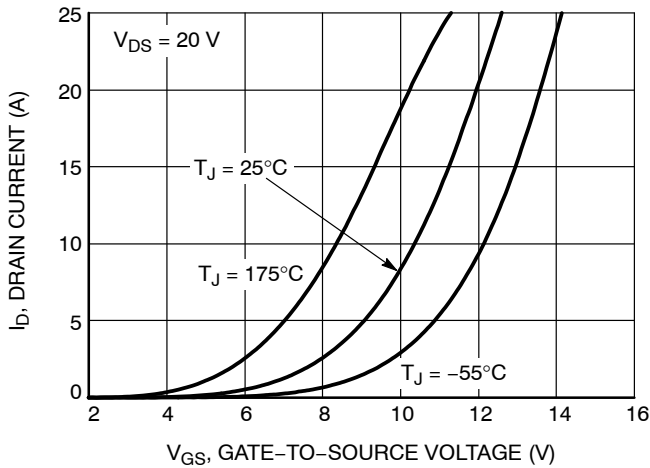


Figure 5. Transfer Characteristics

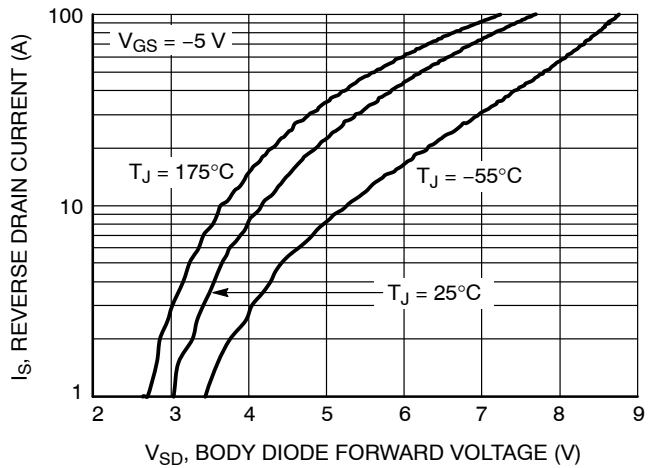


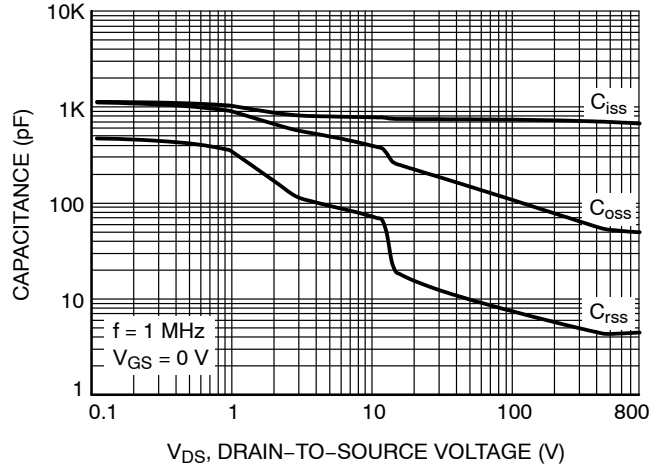
Figure 6. Diode Forward Voltage vs. Current

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## TYPICAL CHARACTERISTICS



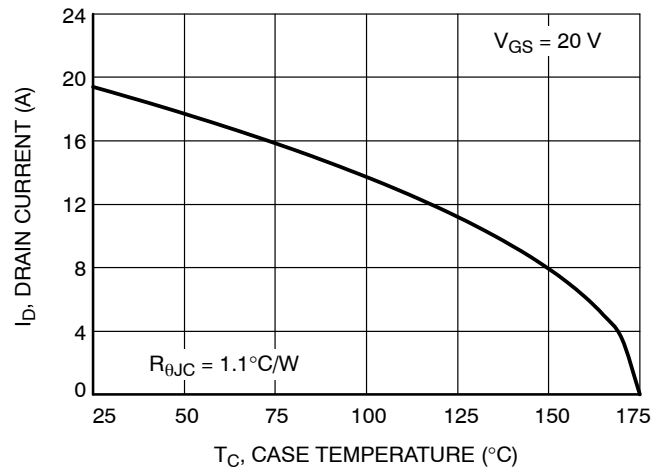
**Figure 7. Gate-to-Source Voltage vs. Total Charge**



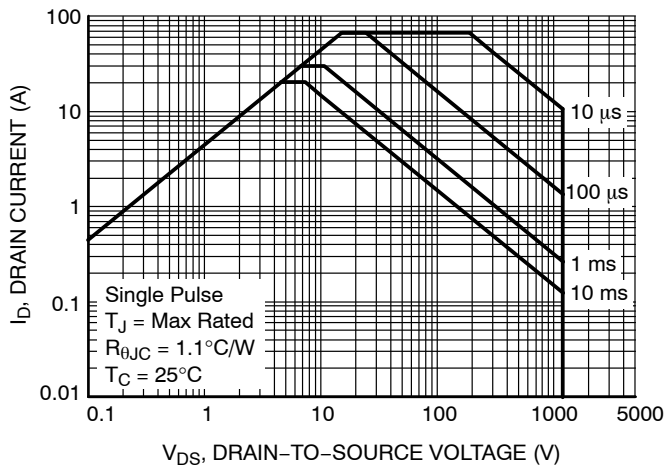
**Figure 8. Capacitance vs. Drain-to-Source Voltage**



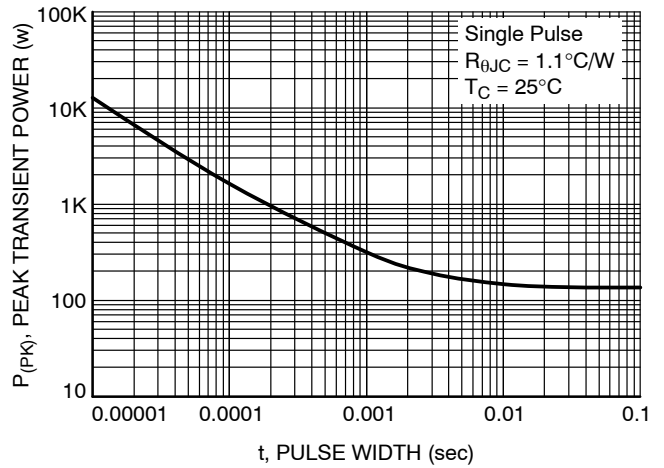
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**



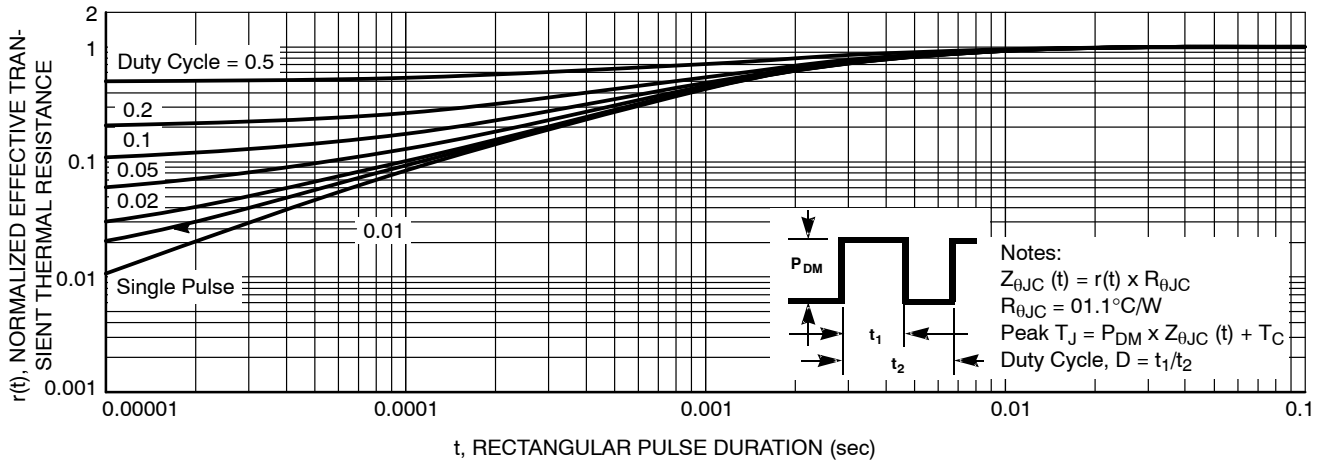
**Figure 11. Safe Operating Area**



**Figure 12. Single Pulse Maximum Power Dissipation**

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## TYPICAL CHARACTERISTICS



**Figure 13. Junction-to-Ambient Transient Thermal Response Curve**

### DEVICE ORDERING INFORMATION

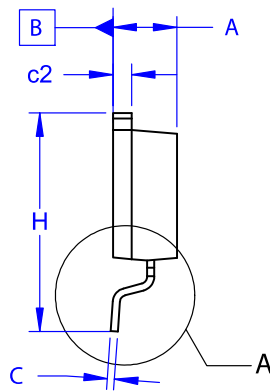
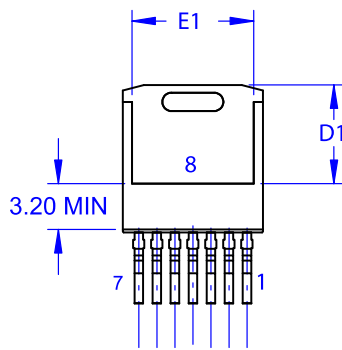
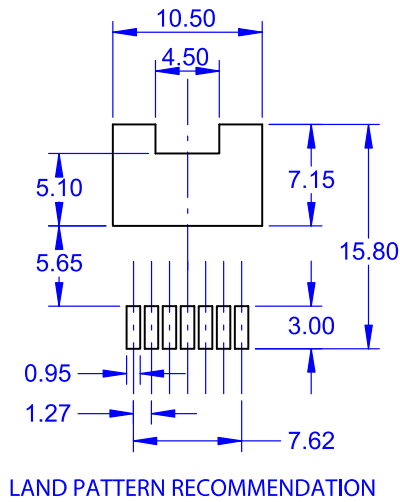
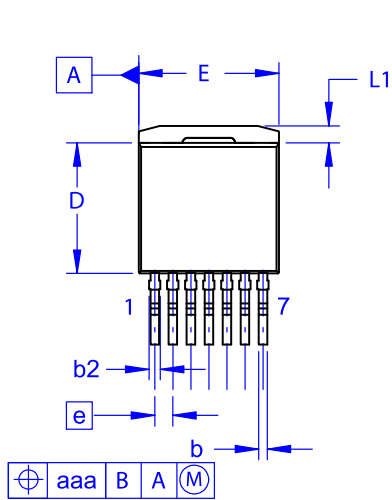
Device	Package	Shipping†
NVBG160N120SC1	D2PAK-7L	800 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## PACKAGE DIMENSIONS

**D<sup>2</sup>PAK7 (TO-263-7L HV)**  
CASE 418BJ  
ISSUE B



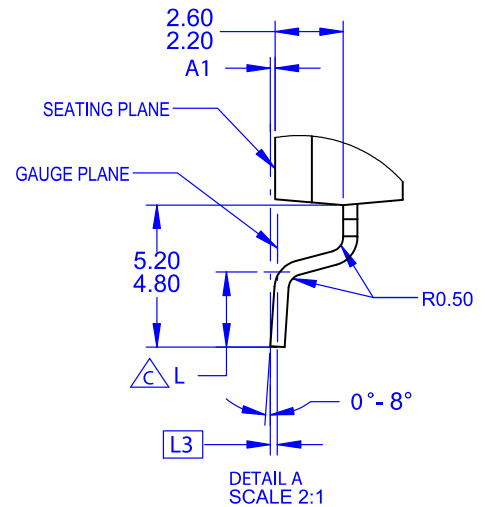
### NOTES:

- A. PACKAGE CONFORMS TO JEDEC TO-263 VARIATION CB EXCEPT WHERE NOTED.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.

△ OUT OF JEDEC STANDARD VALUE.  
D. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.

- E. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	0.00	0.10	0.20
b2	0.60	0.70	0.80
b	0.51	0.60	0.70
c	0.40	0.50	0.60
c2	1.20	1.30	1.40
D	9.00	9.20	9.40
D1	6.15	6.80	7.15
E	9.70	9.90	10.20
E1	7.15	7.65	8.15
e	~	1.27	~
H	15.10	15.40	15.70
L	2.44	2.64	2.84
L1	1.00	1.20	1.40
L3	~	0.25	~
aaa	~	~	0.25



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